Title: Research on Si (100) Crystal Substrate CMP Based on FA/O alkaline slurry

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1. As critical dimensions keep shrinking, the polished silicon surface quality has been improved.

2. Haze was a new and easy control method to monitor the surface quality at wafer scale.

3. The advantages are that Haze is quantitatively collected on full wafer scale with high throughput and it can be collected together with the defects map.

4. The FA/O alkaline slurry is based on FA/O surfactant and FA/O chelating agent. FA/O surfactant has enormous effect on surface roughness and it is better for the particle removal. FA/O chelating agent can decrease the metallic ions residue on surface of the polished wafer.